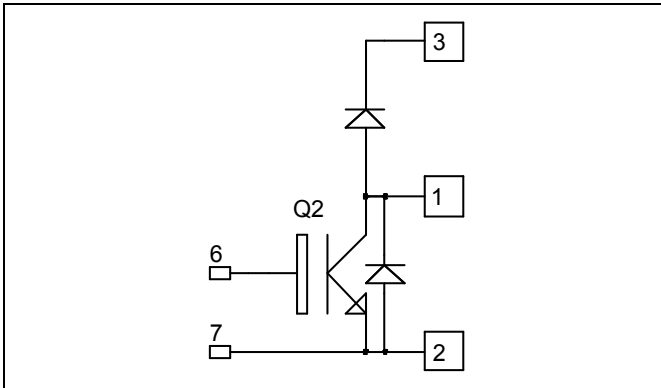


**Boost chopper
Trench + Field Stop IGBT
Power Module**

**$V_{CES} = 1700V$
 $I_C = 200A @ T_c = 80^\circ C$**



Application

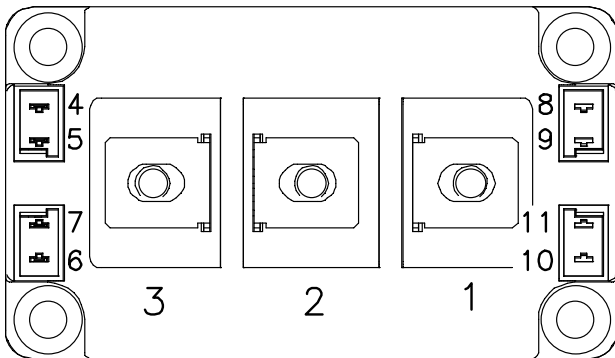
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	310
		$T_C = 80^\circ C$	200
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	1250
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	400A@1650V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1700\text{V}$			3	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$ $I_C = 200\text{A}$	$T_j = 25^\circ\text{C}$	2.0	2.5	V
			$T_j = 125^\circ\text{C}$	2.4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 8\text{mA}$	5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$		18		nF
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.6		
Q_G	Gate charge	$V_{GE} = \pm 15\text{V}, I_C = 200\text{A}$ $V_{CE} = 900\text{V}$		2.3		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 200\text{A}$ $R_G = 6.8\Omega$		280		ns
T_r	Rise Time			80		
$T_{d(off)}$	Turn-off Delay Time			850		
T_f	Fall Time			120		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 200\text{A}$ $R_G = 6.8\Omega$		300		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			1000		
T_f	Fall Time			200		
E_{on}	Turn On Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 900\text{V}$	$T_j = 25^\circ\text{C}$	58		mJ
			$T_j = 125^\circ\text{C}$	78		
E_{off}	Turn Off Energy	$I_C = 200\text{A}$ $R_G = 6.8\Omega$	$T_j = 25^\circ\text{C}$	43		mJ
			$T_j = 125^\circ\text{C}$	63		
I_{sc}	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 1000\text{V}$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		800		A

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RRM}	Maximum Reverse Leakage Current	$V_R = 1700\text{V}$			750	μA
					1000	
I_F	DC Forward Current			200		A
V_F	Diode Forward Voltage	$I_F = 200\text{A}$	$T_j = 25^\circ\text{C}$	1.8	2.2	V
			$T_j = 125^\circ\text{C}$	1.9		
t_{rr}	Reverse Recovery Time	$I_F = 200\text{A}$ $V_R = 900\text{V}$ $di/dt = 3200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	385		ns
			$T_j = 125^\circ\text{C}$	490		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	56		μC
			$T_j = 125^\circ\text{C}$	92		
E_{rr}	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	24		mJ
			$T_j = 125^\circ\text{C}$	48		

Typical Performance Curve

